



Article

# Ambipolar to Unipolar Conversion in C<sub>70</sub>/Ferrocene Nanosheet Field-Effect Transistors

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## Supporting Information

### 1. Experimental Details

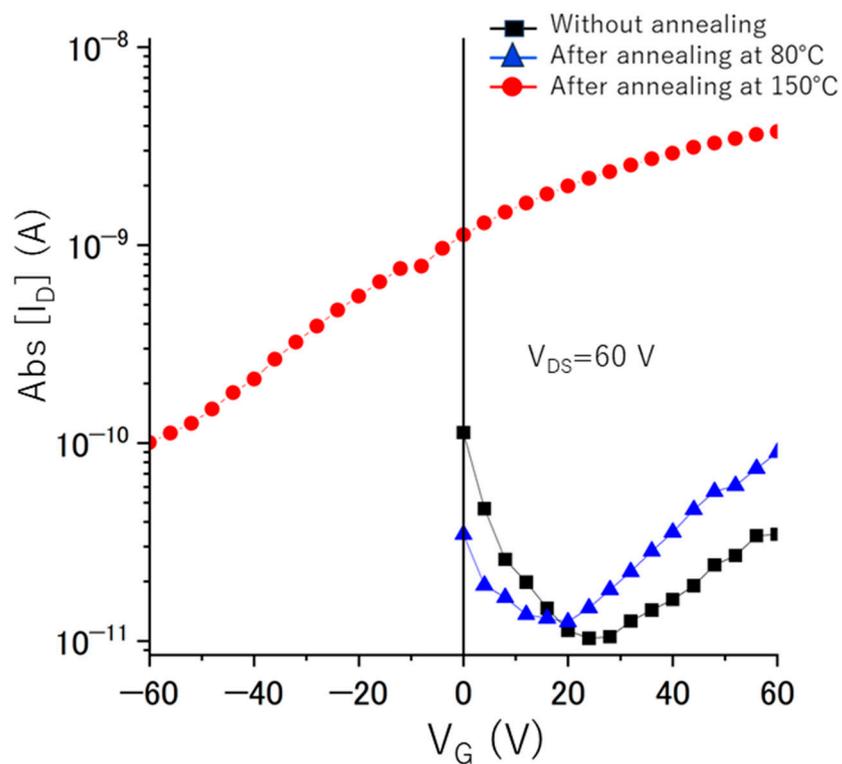
The C<sub>70</sub>/Fc nanosheets were synthesized following the method described in the literature [1]. Firstly, a toluene solution was prepared and saturated with C<sub>70</sub>. Afterward, the solution underwent filtration to eliminate any remaining undissolved C<sub>70</sub> powder. Following that, ferrocene powder was introduced into the C<sub>70</sub>-saturated toluene solution, which was subsequently ultrasonicated in an ice water bath. In a gradual manner, IPA was gently added to the toluene solution, and the resulting mixture was manually shaken. The resulting mixture was then stored at room temperature for a duration of 24 hours, facilitating the growth of C<sub>70</sub>/Fc nanosheets. The nanosheets obtained in this study were thoroughly characterized. Visible/near infrared diffuse reflectance spectroscopy was utilized to investigate the optical properties of the nanosheets. The Photoacoustic Yield Spectrum Analysis (PYSA) was performed using the advanced RIKEN KEIKI AC-3 system, equipped with a monochromated D2 lamp. These comprehensive characterization techniques provide valuable information about the nanosheets, contributing to a better understanding of their potential applications.

### 2. Fabrication of FET devices

The fabrication process of the FET (Field-Effect Transistor) devices involved depositing solutions of C<sub>70</sub>/Fc nanosheets onto prepatterned substrates. The prepatterned substrates consisted of heavily doped Si wafers as gate electrodes, with a gate dielectric layer of thermally oxidized SiO<sub>2</sub> measuring 300 nm in thickness. Gold electrodes were used as the source and drain, with channel lengths ranging from 2–10 μm and widths of 10,000 μm. The preparation of these substrates was conducted at the NIMS NAMIKI Foundry. Electrical transport properties of the devices were measured using a semiconductor analyzer (Agilent B2902A, Agilent E5272A) inside a controlled environment glove box.

## References

1. Osonoe, K.; Kano, R.; Miyazawa, K.; Tachibana, M. Synthesis of C70 two-dimensional nanosheets by liquid-liquid interfacial precipitation method. *J. Cryst. Growth*. **2014**, *401*, 458–461.



**Fig. S1.** Transfer ( $I_D$ - $V_G$ ) characteristics of C<sub>70</sub>/Fc nanosheets in the dark after annealing.